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**LE3.2** 

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**■** Calculator

LE3.2.1: CMOS Recipe

4/4 points (ungraded)
When creating CMOS circuits, NFETs can be used in your pullup and pulldown circuitry.

true

false

true

false

rue

false

NFETs are on when their input is low (or 0).

TAPE IS are on when their input is low (or t

true
false



PFETs are on when their input is low (or 0).



### Explanation

In CMOS circuits, NFETs are used for your pulldown circuitry, and PFETs are used for your pullup circuitry. NFETs are on when their input, or gate, is high (1). PFETs are on when their input, or gate, is low (0).

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**1** Answers are displayed within the problem

### LE3.2.2: Inverter Rise and Fall Times

2 points possible (ungraded)

In the last video, we examined the CMOS inverter circuit consisting of a single PFET pullup connecting the output node to  $V_{DD}$  and single NFET pulldown connecting the output node to GROUND.

When the inverter's input is a digital 0, the PFET pullup is on and the NFET pulldown is off, so the voltage of the output Z rises until it reaches  $V_{DD}$ , a digital 1. The *rise time* of the output is defined as the amount of time it takes for the output voltage to rise from  $V_{OL}$  to  $V_{OH}$ .

When the inverter's input is a digital 1, the PFET pullup is off and the NFET pulldown is on, so the voltage of the output Z falls until it reaches GROUND, a digital 0. The *fall time* of the output is defined as the amount of time it takes for the output voltage to fall from  $V_{OH}$  to  $V_{OL}$ .

In both cases, the transition time is inversely proportional to the  $I_{DS}$  of the conducting MOSFET switch: the greater  $I_{DS}$ , the smaller the transition time. If a designer wanted to change the inverter's design to decrease the rise time, i.e., have output voltage transition more quickly to a digital 1 value, she could (select the best answer): decrease the WIDTH of the NFET pulldown increase the WIDTH of the NFET pulldown decrease the WIDTH of the PFET pullup increase the WIDTH of the PFET pullup If a designer wanted to change the inverter's design to decrease the fall time, i.e., have output voltage transition more quickly to a digital 0 value, she could (select the best answer): decrease the WIDTH of the NFET pulldown increase the WIDTH of the NFET pulldown decrease the WIDTH of the PFET pullup increase the WIDTH of the PFET pullup Submit Discussion **Hide Discussion** Topic: 3. CMOS / LE3.2 **Add a Post** Show all posts **\** by recent activity 🗸 Why does increasing width increase gain? 6 I'm not sure why increasing width decreases rise/fall time. Is it because a wider electric field allows for more current or the depletio... Previous Next >

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